

ELFys PD25s

Photodetector Datasheet



1. Product Description and Key Features

ELFys PD series photodiode products consist of ELFys patented Black Silicon Induced Junction Technology. Product patent information can be found at <https://www.elfys.fi/index.php/technology/patent/>. ELFys PD series photodiode products provide superior performance in photosensitivity across a wide spectrum of wavelengths, from deep UV, Vis to NIR. ELFys PD series photodiode products are suitable for various high precision photometry applications.

Key features:

- Enhanced photosensitivity to UV, Vis and NIR
- H model provides low capacitance
- M model provides low dark current
- G presents the Guard ring design which offers capability of working under high reverse bias voltage with low dark current.

Part number	Photosensitive area (mm)	Chip Outline Dimension (mm)	Reverse Voltage (V) Max.	Guard ring connection	Packaging Options	Window / Filter Options
PD25sH	5.0 x 5.0	6.0 x 6.0	20	No	Chip / PCB / TO-8	No window / Schott UV-glass
PD25sM		6.3 x 6.3	100	Yes	Chip / PCB	No window
PD25sHG						
PD25sMG						

Note: The environmental protection of the photodetector depends on the selected packaging option. ELFys provides customized packaging solutions based on customer specifications.

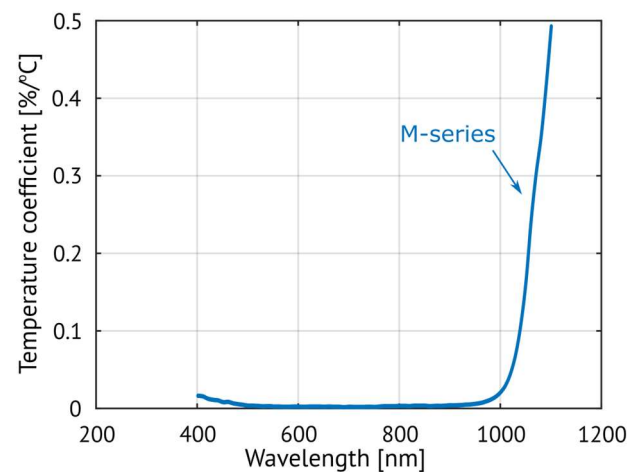
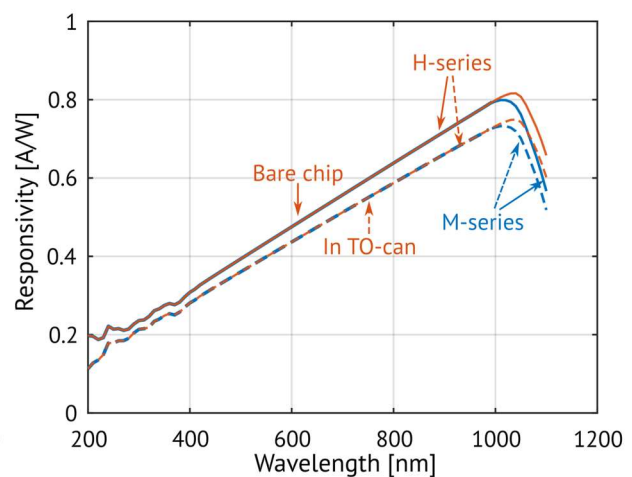
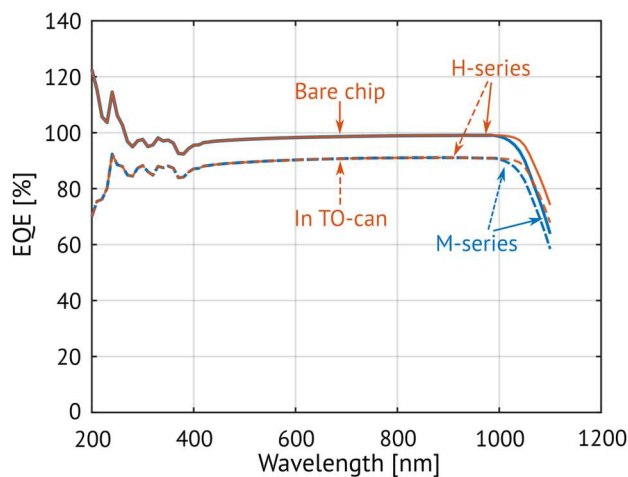


2. Electrical and Optical Performance

Part number	Spectral response range	Peak response wavelength, λ_p	Photosensitivity				Dark current @ $V_R=10\text{mV}$, Max.	Capacitance @ $V_R=0\text{V}$, $f=100\text{kHz}$, Typ.	Shunt resistance @ $V_R=10\text{mV}$, Min.	Noise equivalent power NEP @ λ_p , Max.
			λ_p Typ.	200 nm Typ.	630 nm Typ.	930 nm Typ.				
	nm	nm	A/W	A/W	A/W	A/W	μA	pF	M Ω	W/Hz
PD25sH	170-1100	1040	0.81	0.20	0.50	0.74	700	110	14	4.4×10^{-14}
PD25sHG										
PD25sM		1010	0.80	0.73	30	370	330	9.2×10^{-15}		
PD25sMG										

Note: All data are specified at typical ambient temperature (25°C) and under normal working conditions. Photosensitivity performance will be affected by the optical properties of the window and filter applied in the packaging or end application. Photodiode characteristics, including photosensitivity may degrade when exposed to UV below 240nm. Potential degradation depends on total exposure dose and ambient conditions.

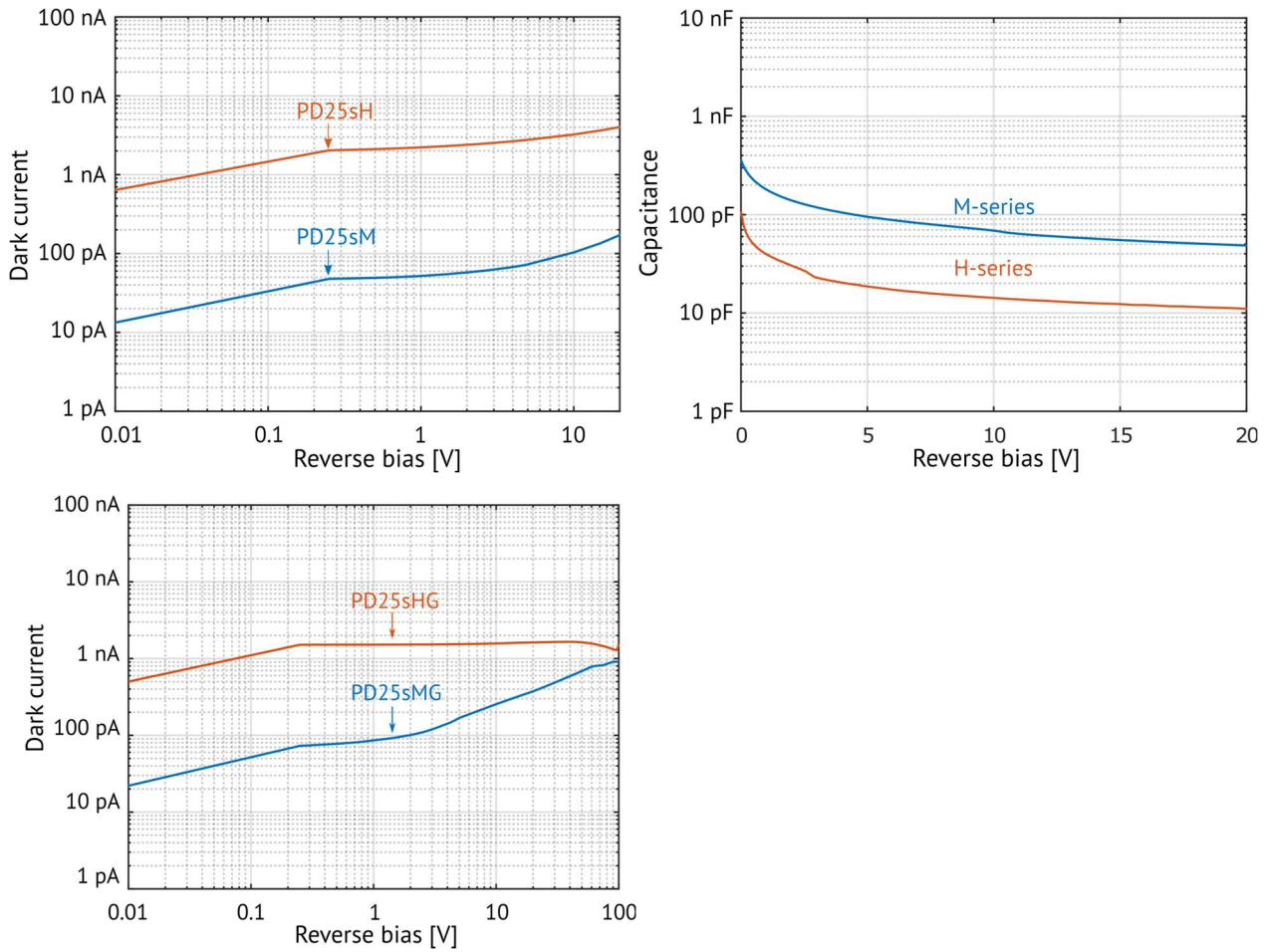
3. Spectral Response (Typical)



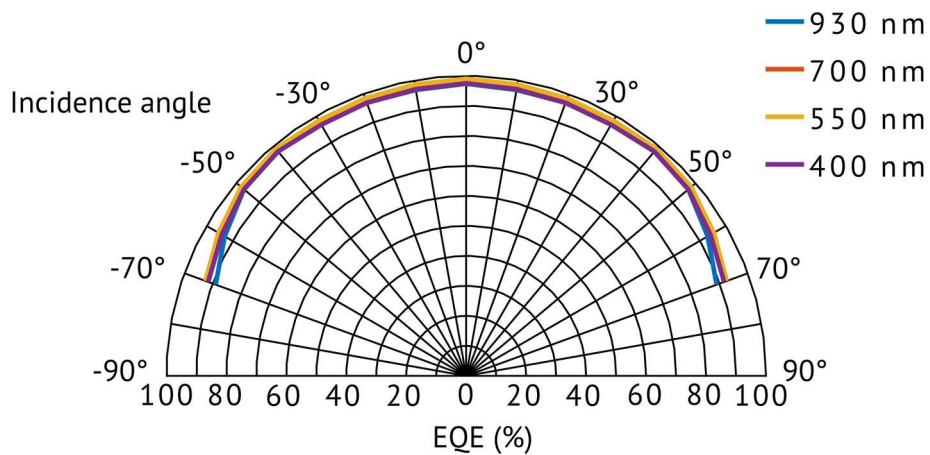
Note: the temperature coefficient in the range 200-400 nm can be provided upon customer request.



4. Dark Current and Capacitance vs Reverse Bias (Typical)



5. Angular responsivity



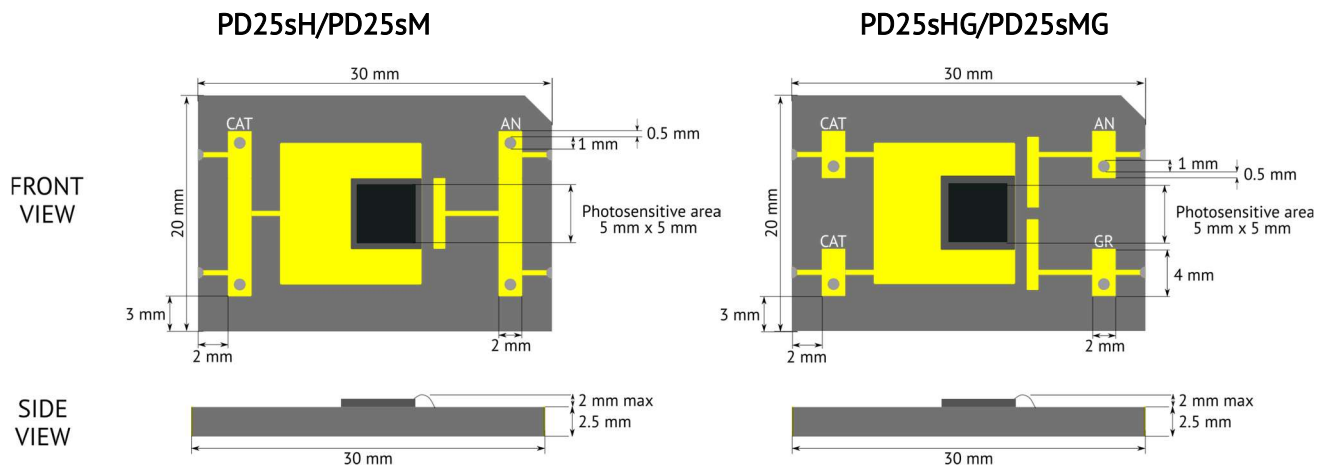
Note: Angle-dependent photosensitivity is measured from a process control monitor photodiode without window or filter.



6. Packaging options

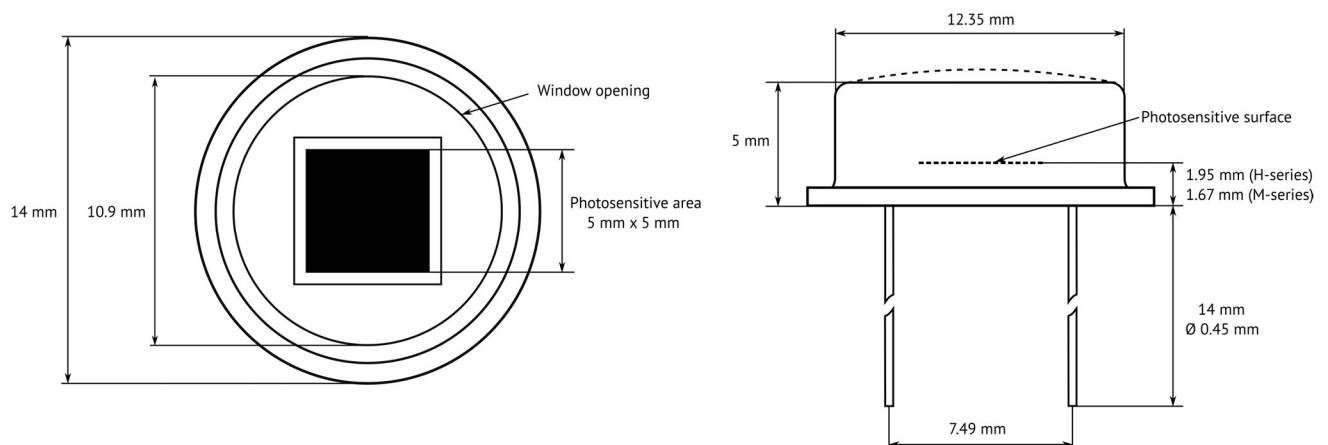
PCB

The photodetector is available by default on a demonstration board (30mm x 20mm). Customized demonstration board is available upon request according to customer specifications. The electrical connections for PD25sH and PD25sM are anode (AN) and cathode (CAT); for PD25sHG and PD25sMG the connections are anode (AN), cathode (CAT) and guard ring (GR). The default demonstration board is suitable for Surface Mount, Through Hole Mount, and Soldering Wire.



TO-8

Another packaging option is TO-8 with Schott UV-glass. Other window materials and/or anti-reflective coatings of window are also available upon request. The cathode contact is connected to the body of the can.



ELFys, Inc. reserves the right to change product specification without prior notice.